



STP22NM60 - STP22NM60FP STB22NM60 - STB22NM60-1

N-CHANNEL 600V - 0.19 Ω - 22A TO-220/FP/D²PAK/I²PAK

MDmesh™ Power MOSFET

ADVANCED DATA

TYPE	V _{DSS}	R _{DS(on)}	R _{ds(on)} *Q _g	I _D
STP22NM60	600 V	< 0.25 Ω	7.6 Ω *nC	22 A
STP22NM60FP	600 V	< 0.25 Ω	7.6 Ω *nC	22 A
STB22NM60	600 V	< 0.25 Ω	7.6 Ω *nC	22 A
STB22NM60-1	600 V	< 0.25 Ω	7.6 Ω *nC	22 A

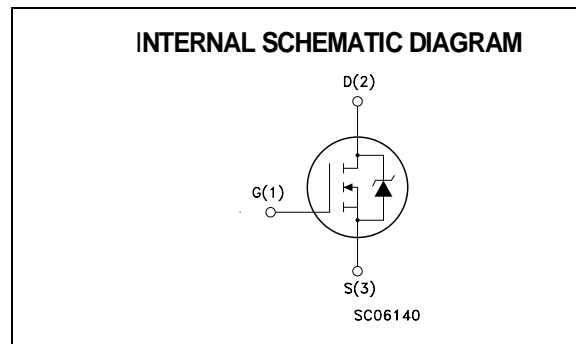
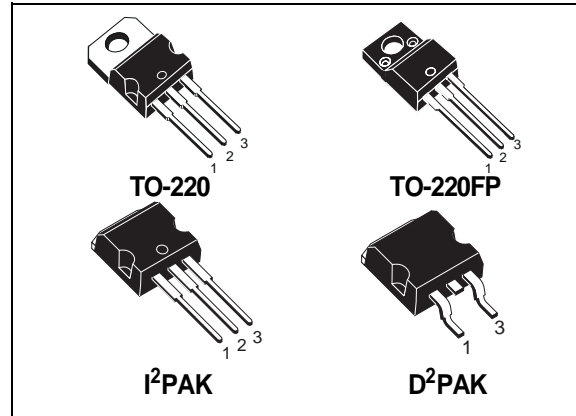
- TYPICAL R_{DS(on)} = 0.19 Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- 100% AVALANCHE TESTED
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE

DESCRIPTION

This improved version of MDmesh™ which is based on Multiple Drain process represents the new benchmark in high voltage MOSFETs. The resulting product exhibits even lower on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall performances that are significantly better than that of similar competition's products.

APPLICATIONS

The MDmesh™ family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP(B)22NM60(-1)	STP22NM60FP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	600		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	600		V
V _{GS}	Gate- source Voltage	±30		V
I _D	Drain Current (continuous) at T _C = 25°C	22	22 (*)	A
I _D	Drain Current (continuous) at T _C = 100°C	12.6	12.6 (*)	A
I _{DM} (●)	Drain Current (pulsed)	80	80(*)	A
P _{TOT}	Total Dissipation at T _C = 25°C	192	45	W
	Derating Factor	1.2	0.36	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	15		V/ns
V _{ISO}	Insulation Withstand Voltage (DC)	--	2500	V
T _{stg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

(●)Pulse width limited by safe operating area

(1)I_{SD} ≤ 22A, di/dt ≤ 400A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

(*)Limited only by maximum temperature allowed

STP22NM60 / STP22NM60FP / STB22NM60 / STB22NM60-1

THERMAL DATA

			TO-220/D ² PAK/I ² PAK	TO-220FP	
Rthj-case	Thermal Resistance Junction-case	Max	0.65	2.8	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5		°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	11	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	650	mJ

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	600			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±30 V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3	4	5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V, I _D = 11 A		0.19	0.25	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 11 A		TBD		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		1590		pF
C _{oss}	Output Capacitance			803		pF
C _{rss}	Reverse Transfer Capacitance			52		pF
C _{oss eq.} (2)	Equivalent Output Capacitance	V _{GS} = 0V, V _{DS} = 0V to 400V		130		pF
R _g	Gate Input Resistance	f=1 MHz Gate DC Bias=0 Test Signal Level=20mV Open Drain		1.6		Ω

1. Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.

2. C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.



ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 200\text{ V}$, $I_D = 11\text{ A}$ $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		25		ns
t_r	Rise Time			20		ns
Q_g	Total Gate Charge	$V_{DD} = 400\text{ V}$, $I_D = 22\text{ A}$, $V_{GS} = 10\text{ V}$		40	71	nC
Q_{gs}	Gate-Source Charge			11		nC
Q_{gd}	Gate-Drain Charge			25		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 480\text{ V}$, $I_D = 22\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 5)		13		ns
t_f	Fall Time			15		ns
t_c	Cross-over Time			26		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				20	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				80	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 22\text{ A}$, $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 22\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 100\text{ V}$, $T_j = 25^\circ\text{C}$ (see test circuit, Figure 5)		416		ns
Q_{rr}	Reverse Recovery Charge			5.6		μC
I_{rrm}	Reverse Recovery Current			27		A
t_{rr}	Reverse Recovery Time	$I_{SD} = 22\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 100\text{ V}$, $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		544		ns
Q_{rr}	Reverse Recovery Charge			7.3		μC
I_{rrm}	Reverse Recovery Current			28		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

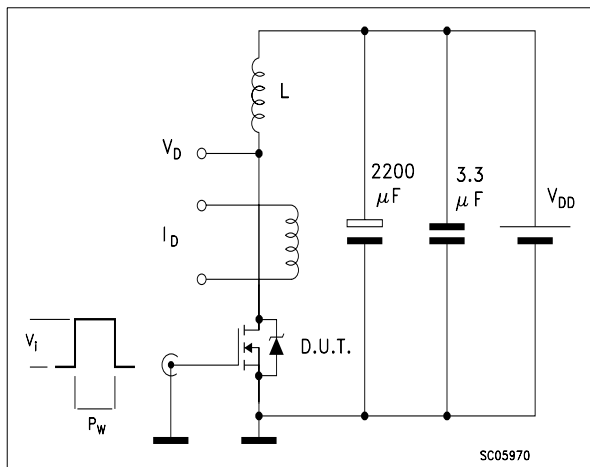


Fig. 2: Unclamped Inductive Waveform

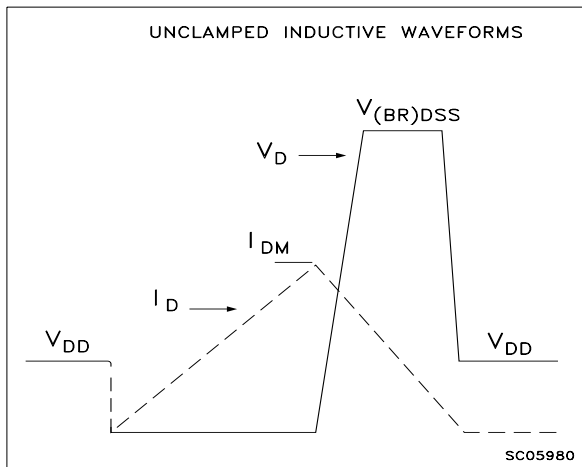


Fig. 3: Switching Times Test Circuits For Resistive Load

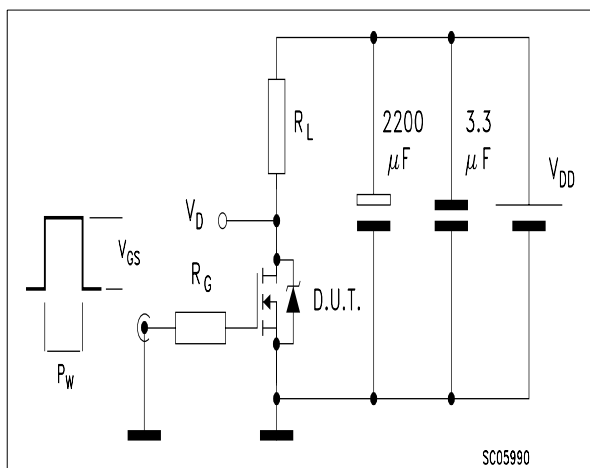


Fig. 4: Gate Charge test Circuit

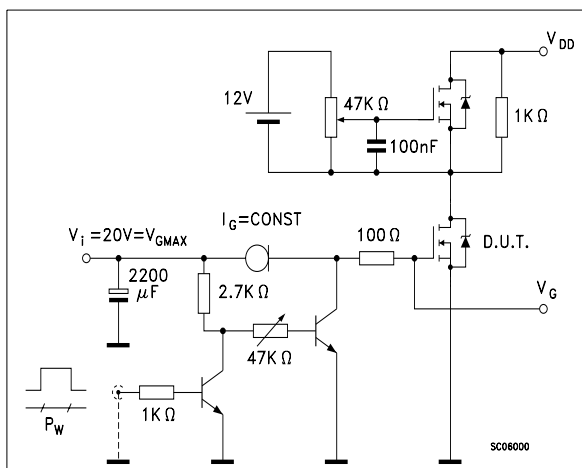
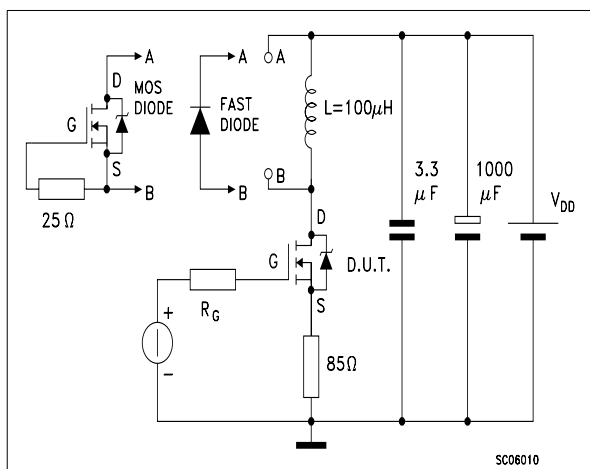
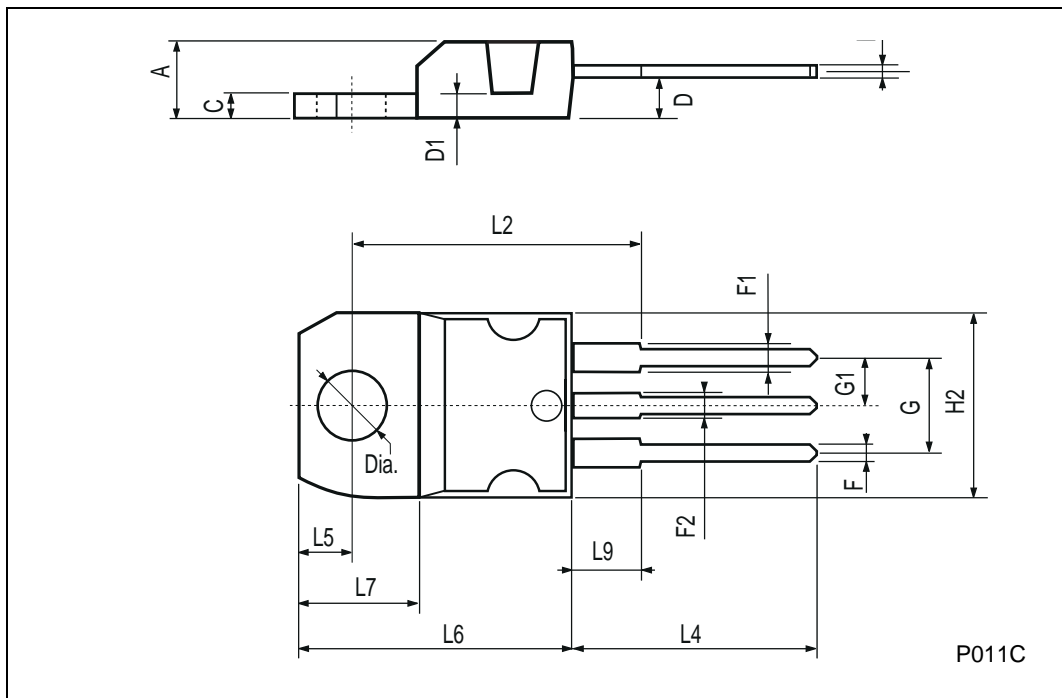


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



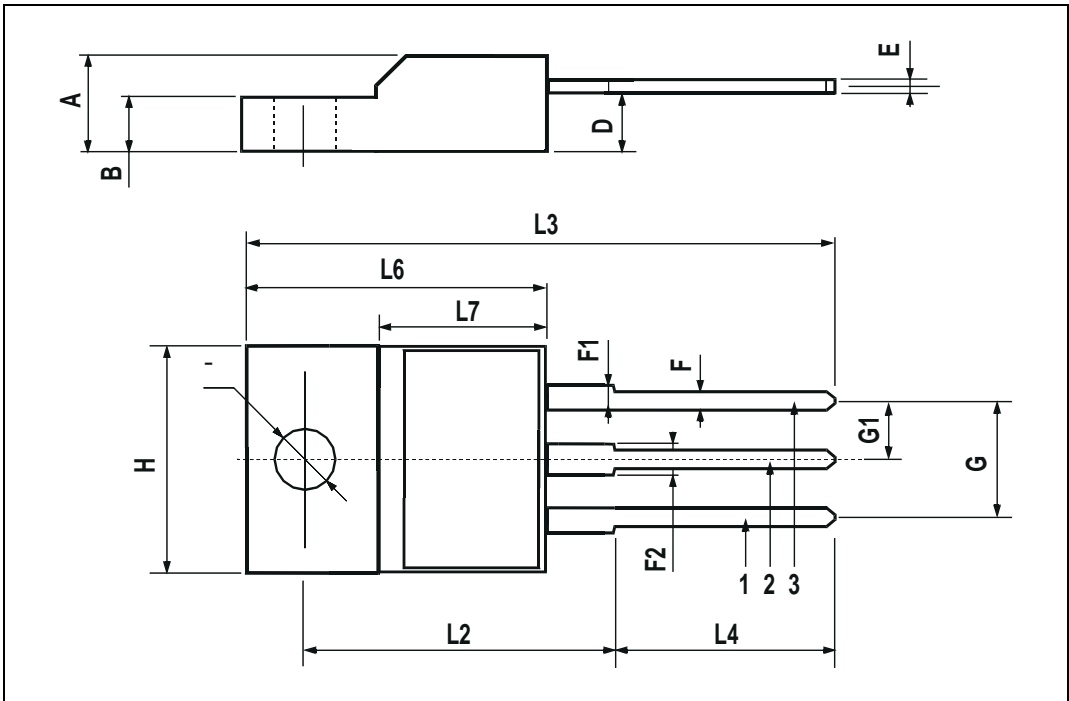
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



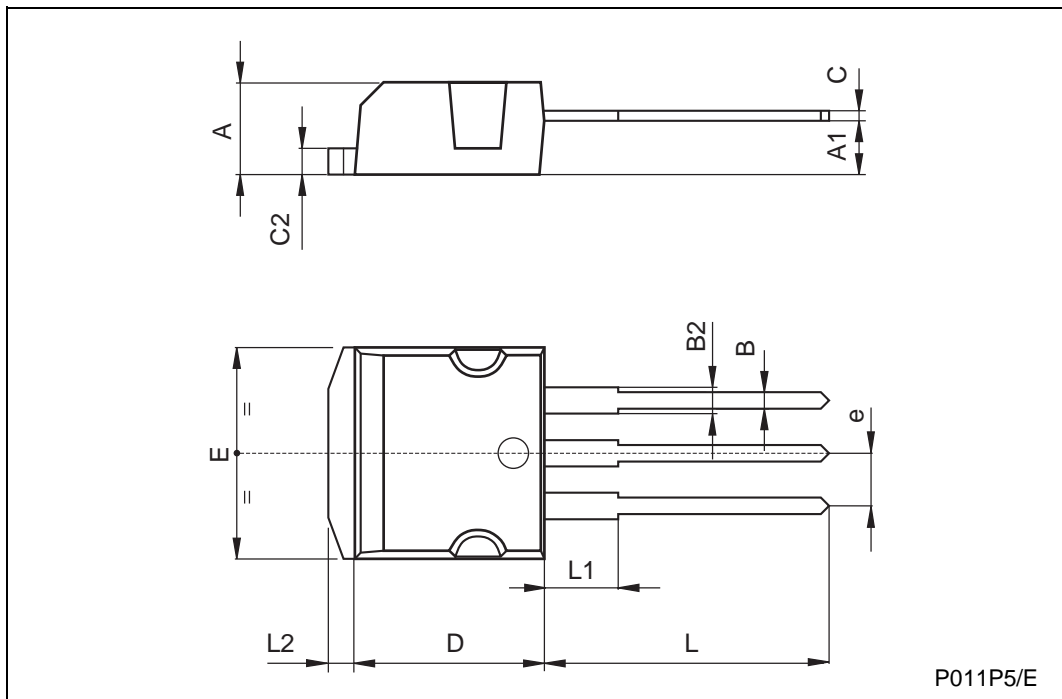
TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
∅	3		3.2	0.118		0.126



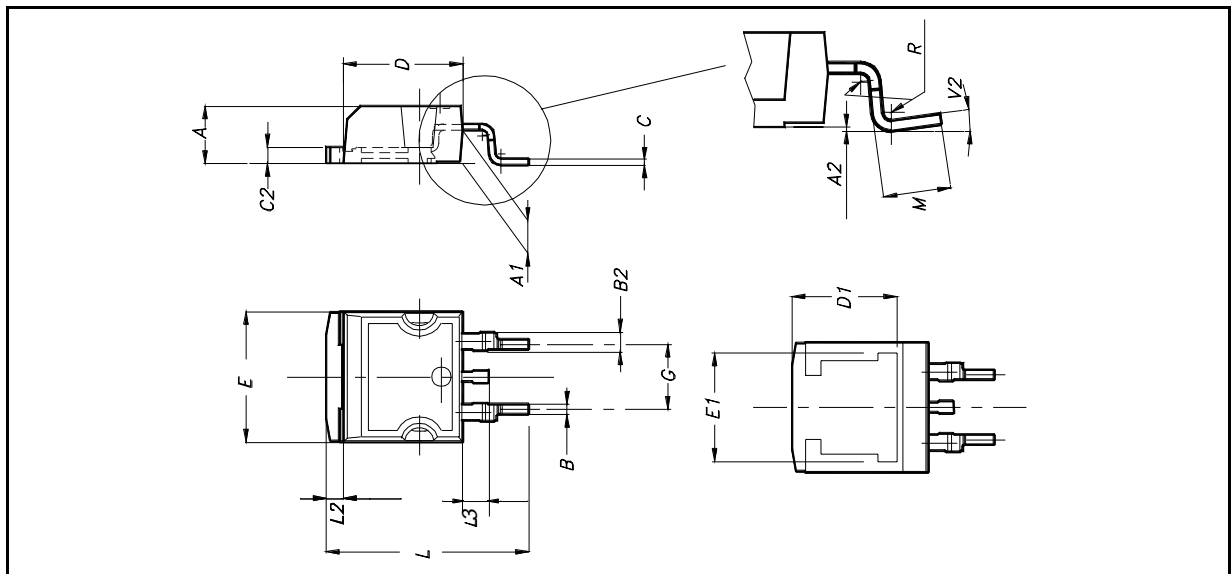
TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
e	2.4		2.7	0.094		0.106
E	10		10.4	0.393		0.409
L	13.1		13.6	0.515		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.4	0.050		0.055

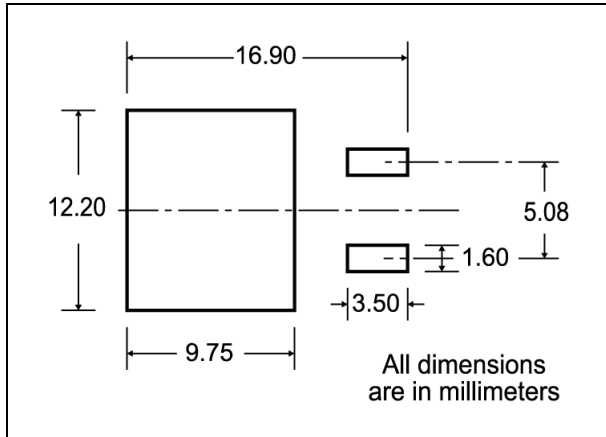


D²PAK MECHANICAL DATA

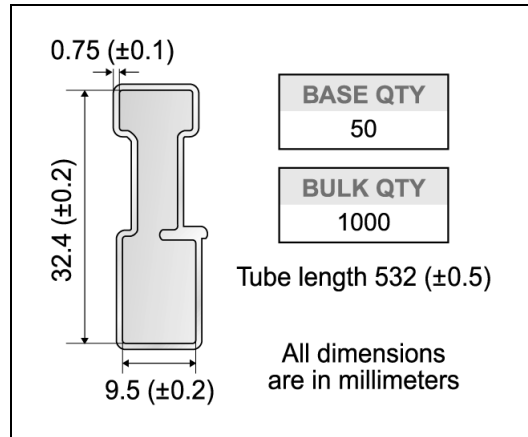
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			



D²PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*

Diagram showing the tape mechanical data. The tape has a width of 40 mm min. Access hole at slot location. The tape slot in the core for tape start has a width of 2.5 mm min. The full radius is indicated. Dimensions A, B, C, D, and G are labeled. G is measured at the hub.

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

Diagram showing the tape and reel shipment details. The top cover tape has a thickness of K₀. The user direction of feed is indicated. The center line of the cavity is shown. The bending radius is R min. The feed direction is indicated. The tape has a width of W and a thickness of T. The pitch of the tape is P₁ and P₂. The distance between the centers of the cavities is A₀. The distance from the center of the cavity to the edge of the tape is B₀. The distance from the center of the cavity to the edge of the tape is D₁. The distance from the center of the cavity to the edge of the tape is E. The distance from the center of the cavity to the edge of the tape is F. The distance from the center of the cavity to the edge of the tape is G. The distance from the center of the cavity to the edge of the tape is H. The distance from the center of the cavity to the edge of the tape is I. The distance from the center of the cavity to the edge of the tape is J. The distance from the center of the cavity to the edge of the tape is K. The distance from the center of the cavity to the edge of the tape is L. The distance from the center of the cavity to the edge of the tape is M. The distance from the center of the cavity to the edge of the tape is N. The distance from the center of the cavity to the edge of the tape is O. The distance from the center of the cavity to the edge of the tape is P. The distance from the center of the cavity to the edge of the tape is Q. The distance from the center of the cavity to the edge of the tape is R. The distance from the center of the cavity to the edge of the tape is S. The distance from the center of the cavity to the edge of the tape is T. The distance from the center of the cavity to the edge of the tape is U. The distance from the center of the cavity to the edge of the tape is V. The distance from the center of the cavity to the edge of the tape is W. The distance from the center of the cavity to the edge of the tape is X. The distance from the center of the cavity to the edge of the tape is Y. The distance from the center of the cavity to the edge of the tape is Z.

* on sales type



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